

# Precision Alignment of Analyzer Gratings for High Energy X-Ray Phase Contrast Imaging



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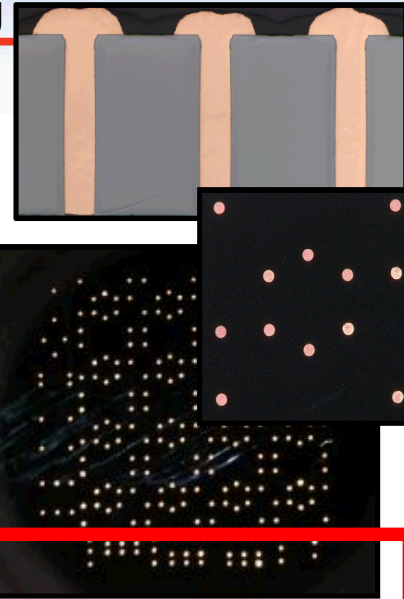




# Mesoscale Fabrication

## Electroplating for Forming, Filling, and Coating

Electroformed 3D Au Stylus Ion Trap Through Full Substrate Via Filling



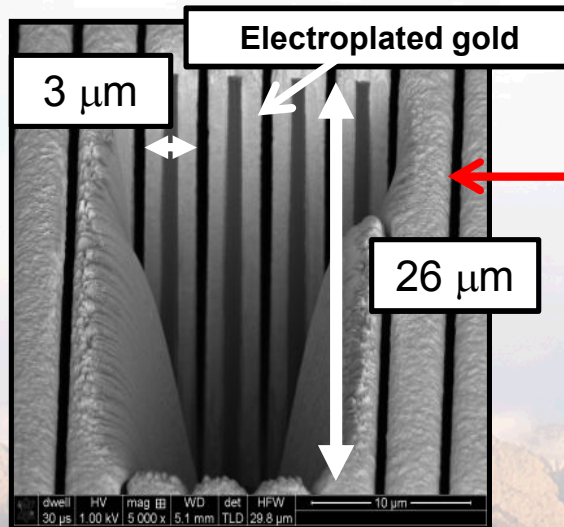
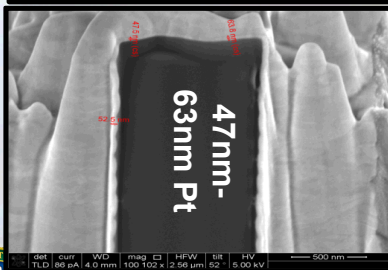
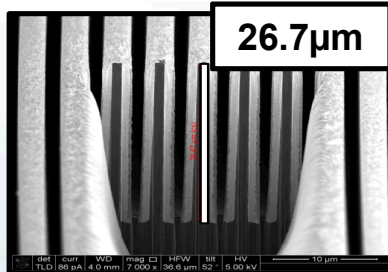
### What is Mesoscale?

*Copper Filled Through Wafer Silicon Vias*

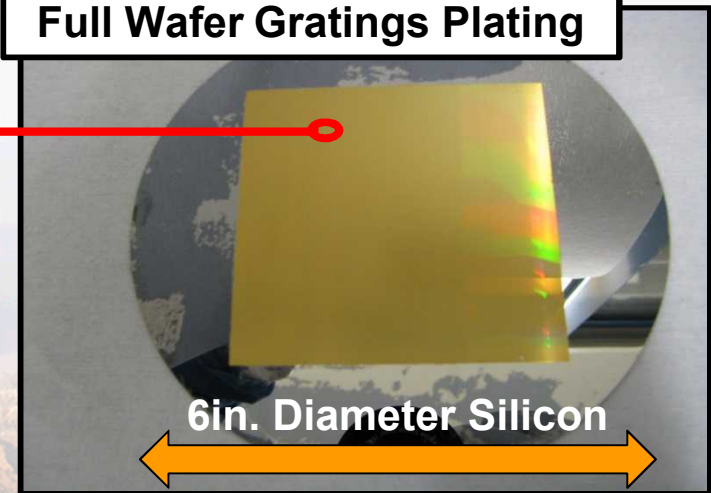
100  $\mu\text{m}$

EHT: 10.00 kV WGT: 3.7 mm Signal A: SE-2

### Precision Electro-coating



### Full Wafer Gratings Plating



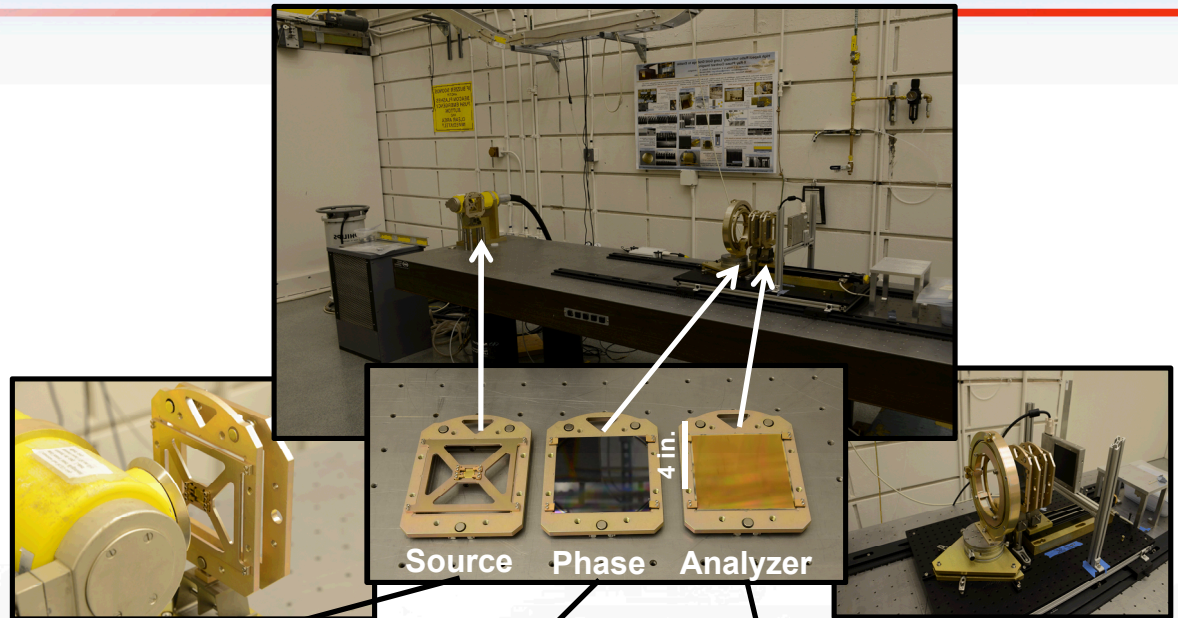
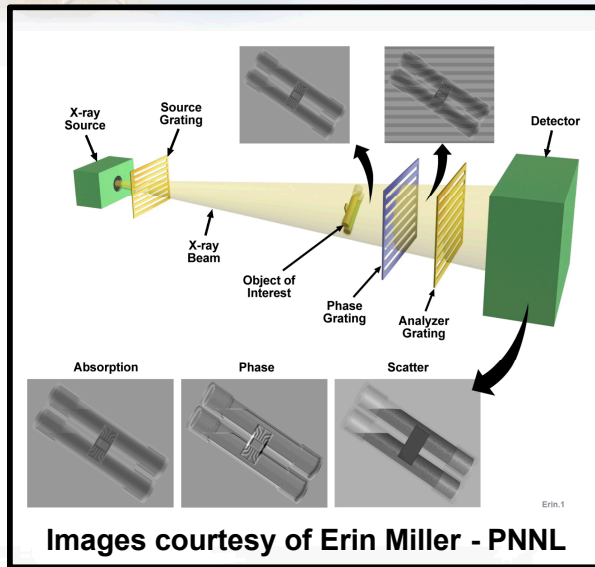


$$n = (1 - \delta) + i \cdot \beta$$

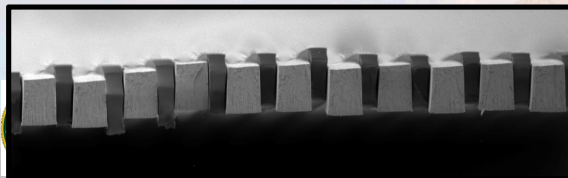
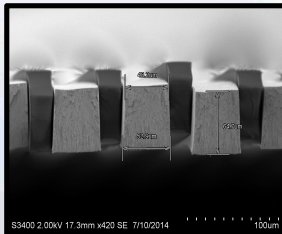
$\beta \rightarrow$  Absorption  $\delta \rightarrow$  Phase  
 $\delta / \beta \sim 10^3$  for low density materials

# Sandia's Three Grating XPCI System

28keV System

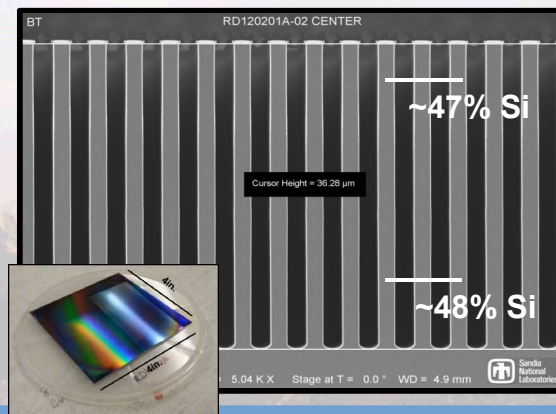


**G0 Source Grating**  
 65  $\mu$ m Thick Au

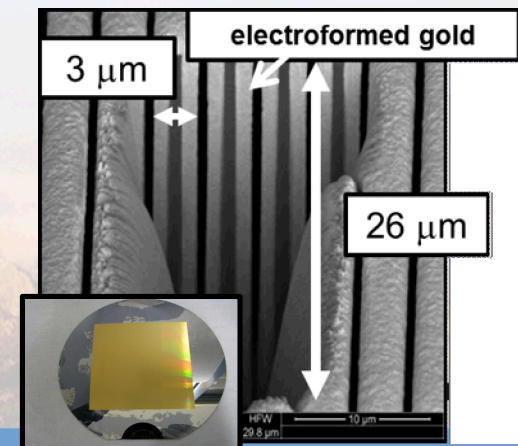


Delamination result of cross-section

**G1 Phase Grating**  
 40  $\mu$ m deep DRIE Si



**G2 Analyzer Grating**  
 26  $\mu$ m Thick Electrocoated Si





# Analyzer Grating Fabrication Through Electrofilling

Aspect Ratios > 20:1 are needed to improve contrast

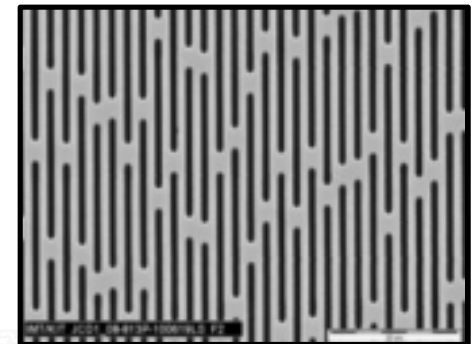
1 $\mu$ m Wide High Z Absorber

50% Grating Duty Cycle

- Resist swelling occurs
- Structural stability of resist is low



Infinite grating length<sup>1</sup>



25 $\mu$ m Length, 3 $\mu$ m wide support bars<sup>1</sup>

Mohr et al. has been able to achieve very impressive aspect ratios as high as 100:1, however this approach is limited through the necessity of support structures or tiling gratings to achieve large area systems.



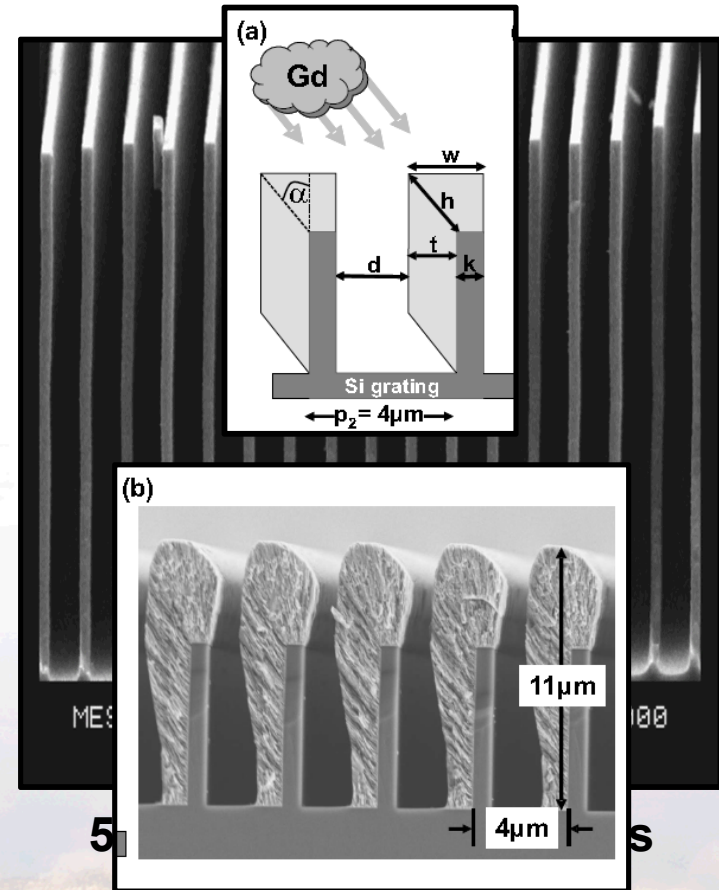
1. Mohr, J., et al., *High Aspect Ratio Gratings for X-Ray Phase Contrast Imaging*. International Workshop on X-Ray and Neutron Phase Imaging with Gratings, 2012. **1466**: p. 41-50.





# Coating Instead of Filling

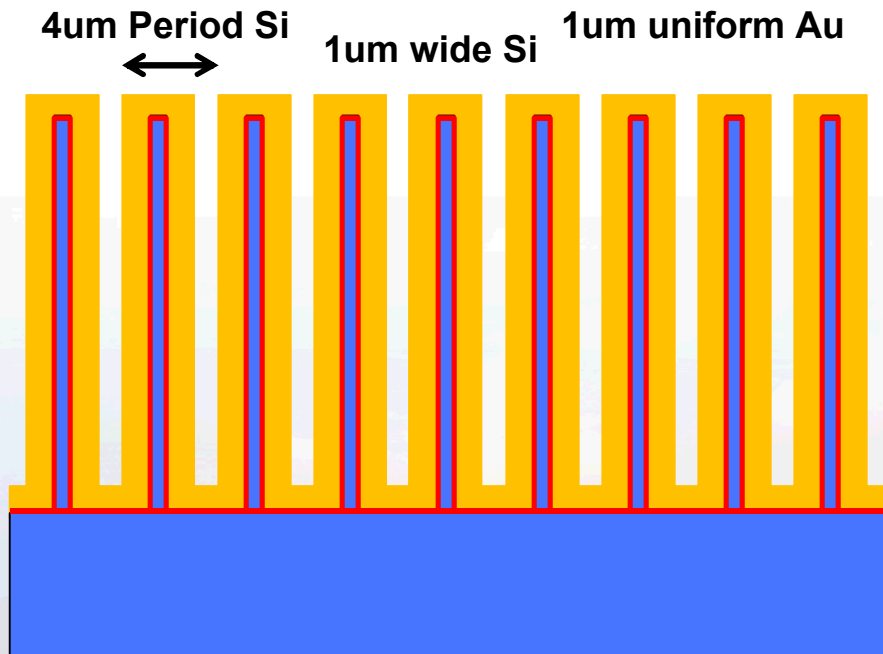
- **Angled RF Sputter Vapor Deposition**
- **highly anisotropic** depositing a wide variety of materials
- **high aspect ratios possible (50:1)**
- **Better surface topography**



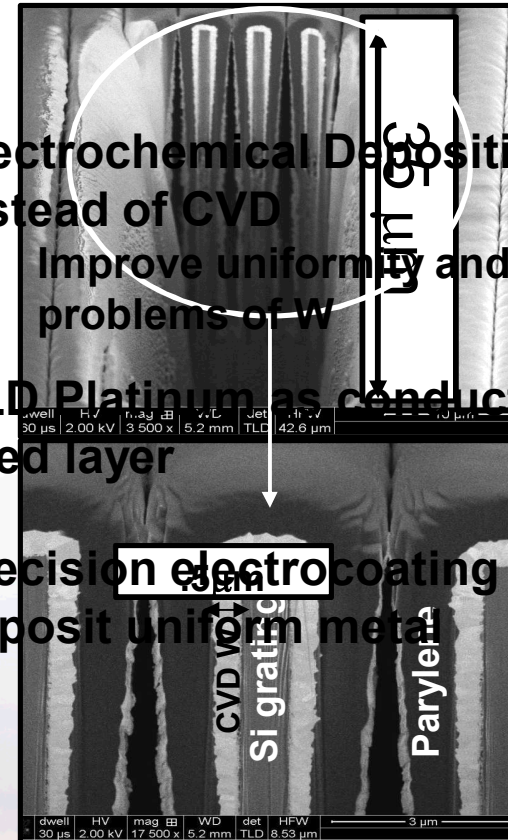


# Electro-coating Instead of Filling

- CVD Tungsten (W) is deposited with very high tensile stress (GPa)
- Non-uniform deposition
- Parylene required for added rigidity



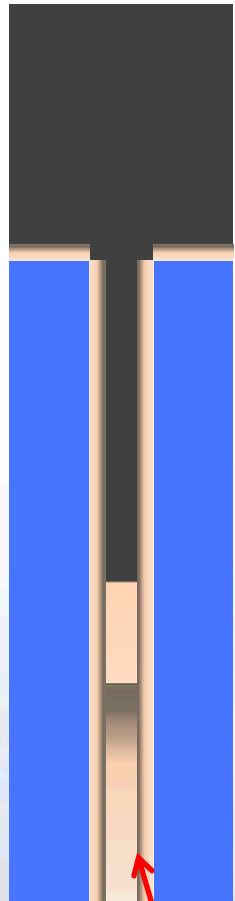
- Electrochemical Deposition instead of CVD
  - Improve uniformity and stress problems of W
- ALD Platinum as conductive seed layer
- Precision electrocoating to deposit uniform metal





# Challenges in Electro-coating vs Filling

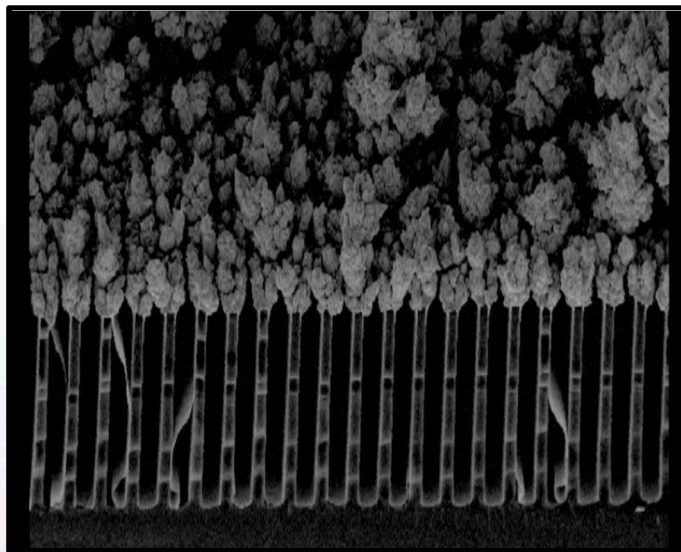
Max (bulk) Ion Concentration



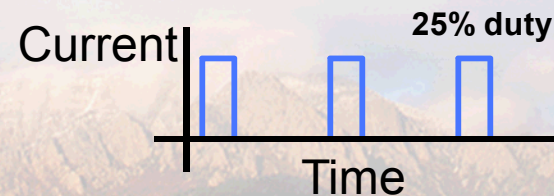
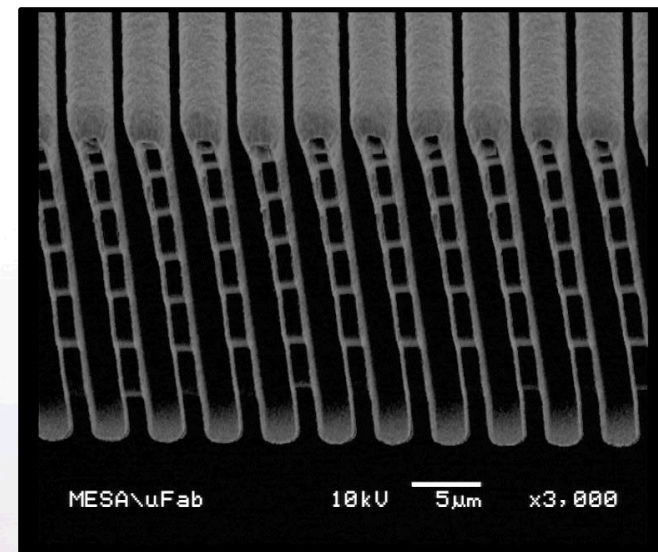
Severely depleted region

- Needs to Improve Plating
- Incorporate more time for ionic replenishment
- Equilibrate concentrations over plating surfaces
- Increase period of time between deposition pulses

DC



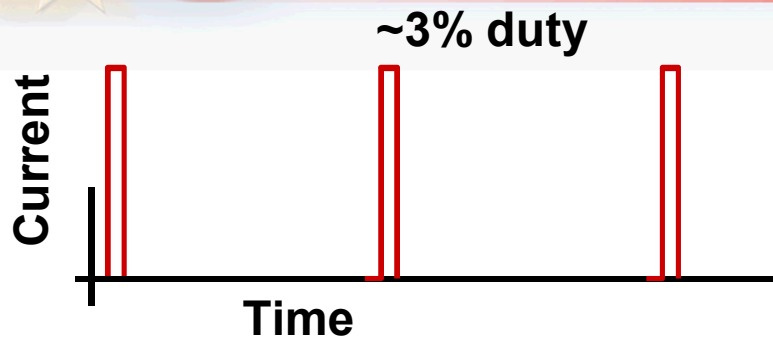
AC



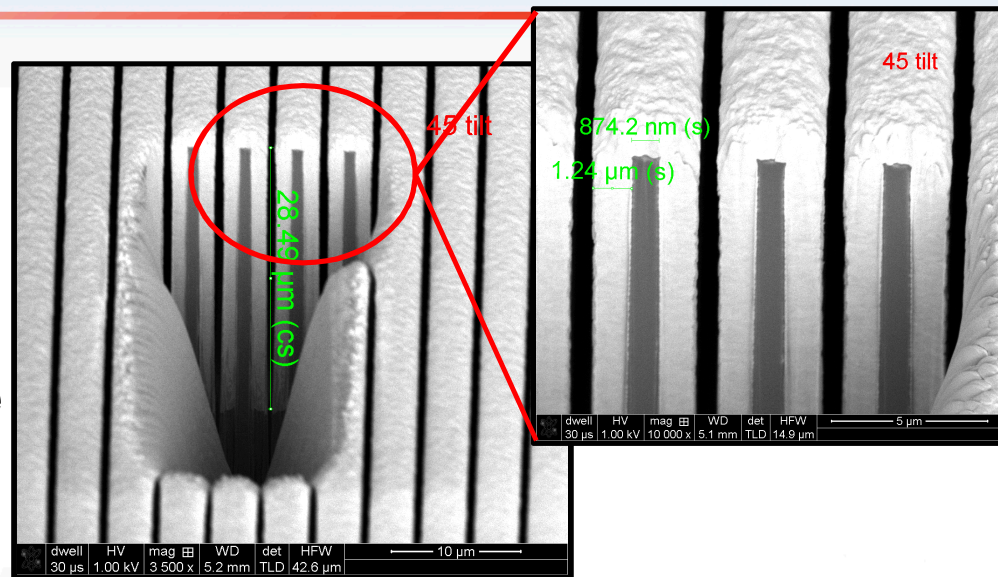
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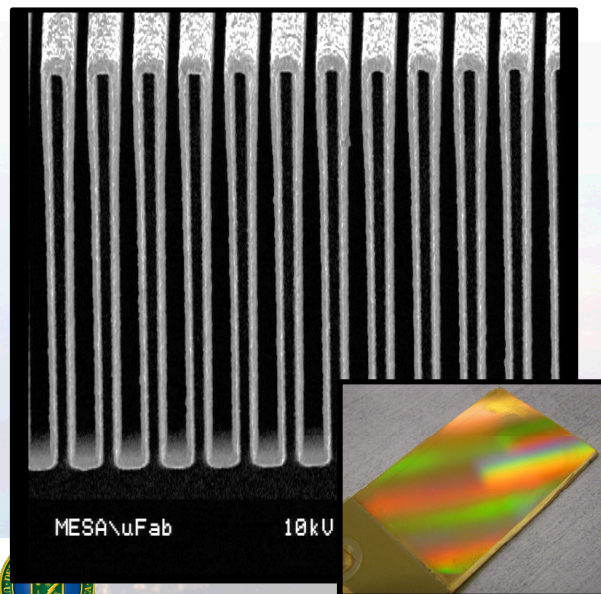
# Optimized Pulse Plating Conditions



Drastically reduced kinetic and plating rate

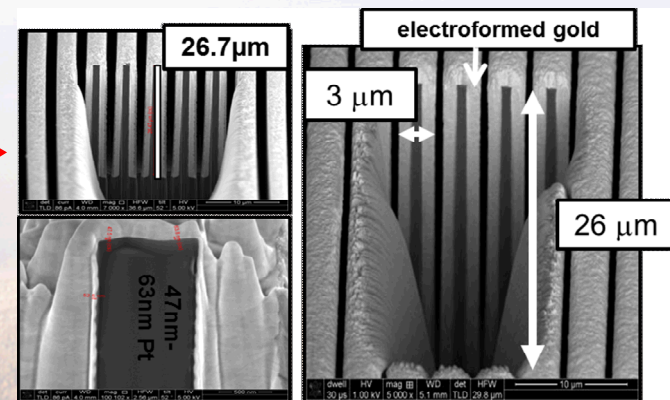
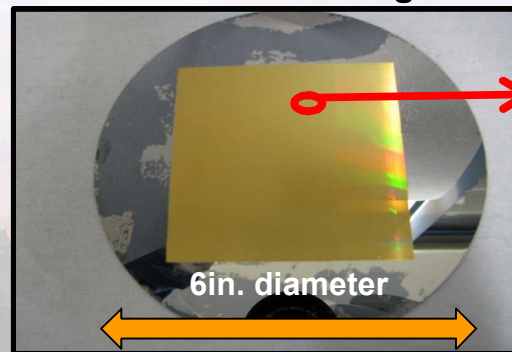


50:1 aspect ratio gratings



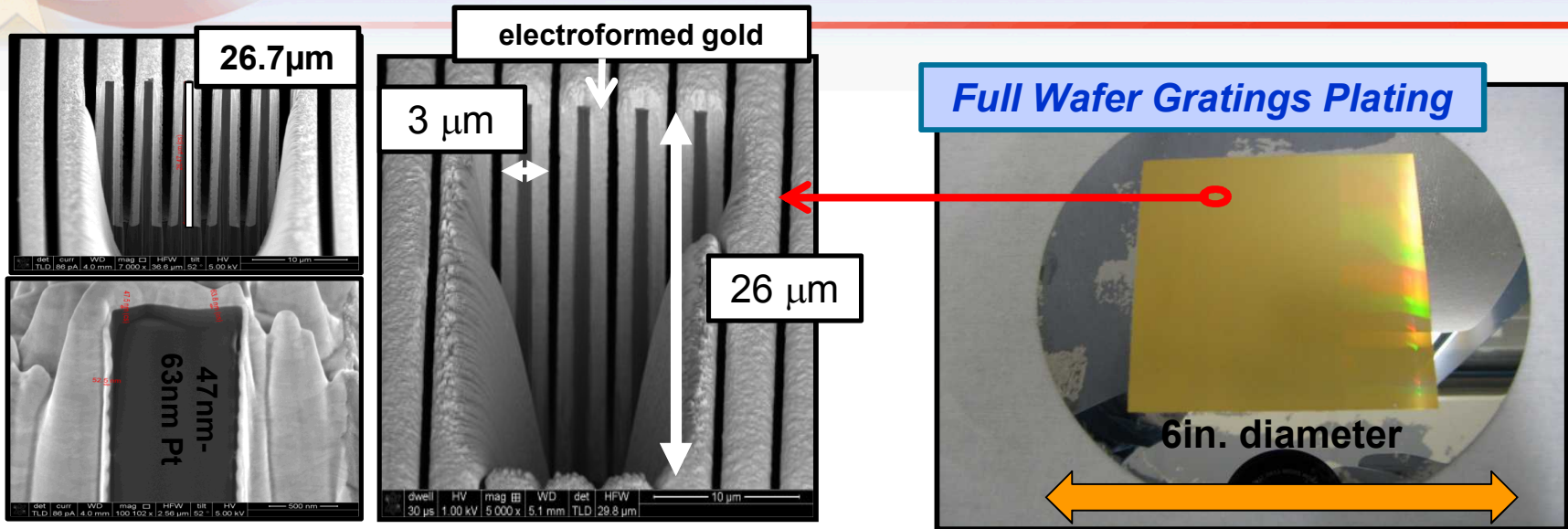
Uniform Plating in 30:1 aspect ratio gratings

Full Wafer Gratings





# Precision Electro-coated Si Gratings



## Bottom-Up Approach (UV or LIGA)

- High aspect ratios possible
- Resist is not structurally stable
- Resist swelling occurs
- FOV is limited

## Tungsten CVD of Si DRIE Gratings

- Non-uniform deposition in high aspect ratios
- Highly stressful
- Parylene required for added rigidity

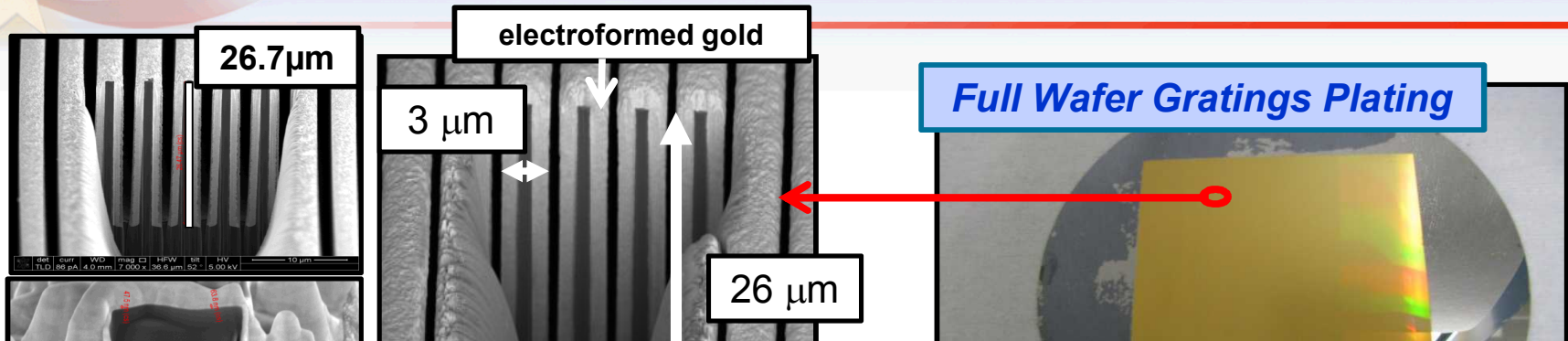
## Electroplating Approach

- High absorber material (Au) is possible
- Uniformity can be tailored to desired aspect ratio
- ALD Pt provides a conformal seed layer
- Low stress Au
- Lateral support structure are not necessary
- 50 μm tall Si gratings have been plated
- 4 in. X 4 in. area achieved with 26 μm tall Si gratings
- Uniform plating process is complex and geometry dependent
- Increasing to larger areas becomes cost inhibited

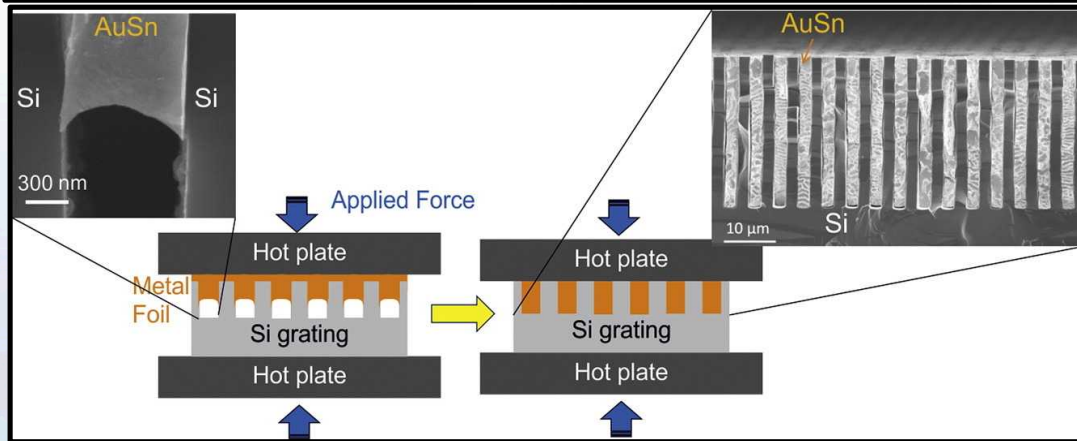




# Precision Electro-coated Si Gratings



**Increasing the aspect ratio of our Si template will allow high energy XPCI systems or alternatively allow cheaper materials to be used on lower energy systems**



## AuSn Embossing into Si template

- Cost effective material
- Less sensitive filling mechanism than electro-coating
- High uniformity is feasible with full wafer bonding tools
- Less dense material requires thicker template
- Higher energy XPCI systems requires thicker template

L. Romano et. al. Microelectronic Engineering 176(2017) 6-10

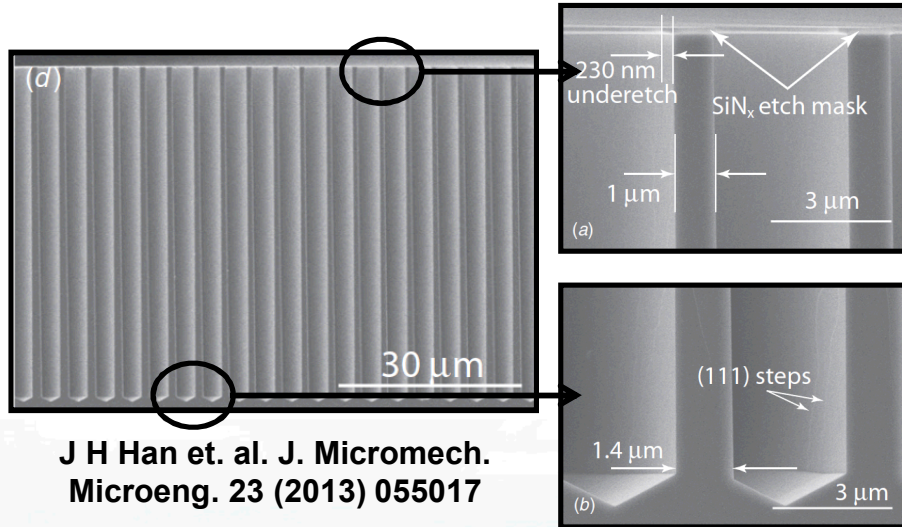


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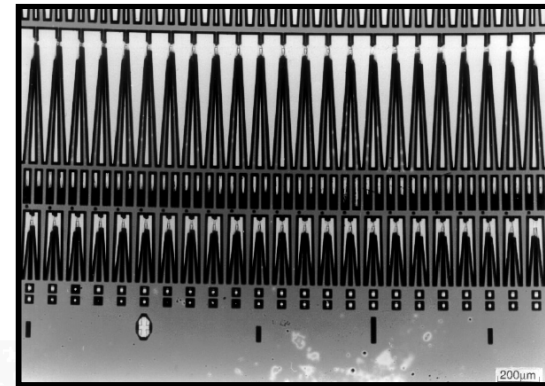
# Alternative Etch for Increasing Aspect Ratio Crystallographic Etching in KOH

Etch selectivities of 600:1 have been reported between [110] and [111] crystal planes

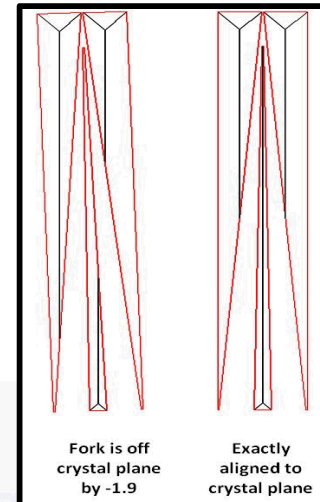


J H Han et. al. J. Micromech. Microeng. 23 (2013) 055017

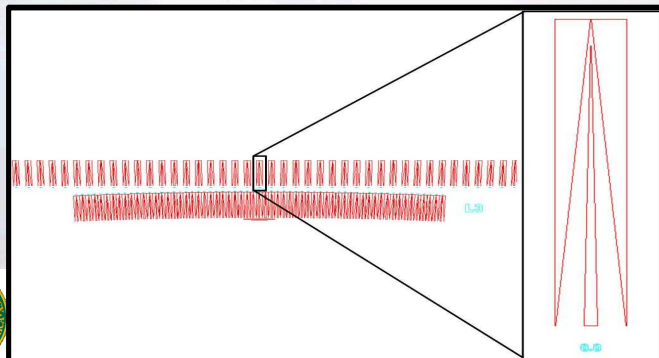
Wafer flats are aligned within 2° of a crystal plane → Need a method for accurate alignment within 0.1°



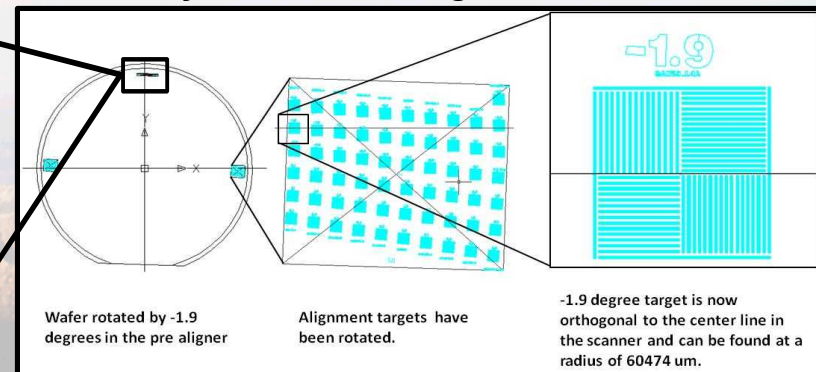
M. Vangbo et. al. J. Micromech. Microeng. 6 (1996) 279-284



Arrayed Comb Structures at 0.1° increments from -3° to +3°



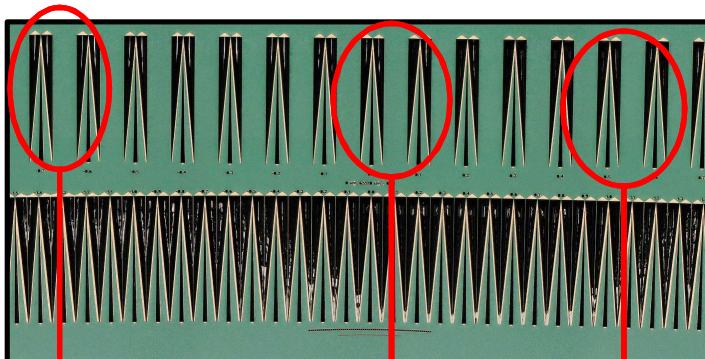
Layer 0 Etch and Alignment Scheme





# Alternative Etch for Increasing Aspect Ratio Crystallographic Etching in KOH

25 minute layer 0 etch in 6 M KOH

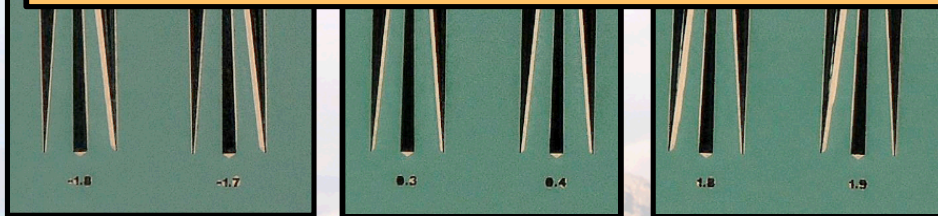


Replace this with an image of a grating etched after performing this alignment

**Stop by Patrick Finnegan's Poster for more information  
on our KOH etching results.**

**Poster #37 Wednesday 13 September 12:30-14:30**

**"Extending the Aspect Ratio of Etched Silicon for Precision Electro-coating with Gold to Fabricate XPCI Analyzer Gratings"**

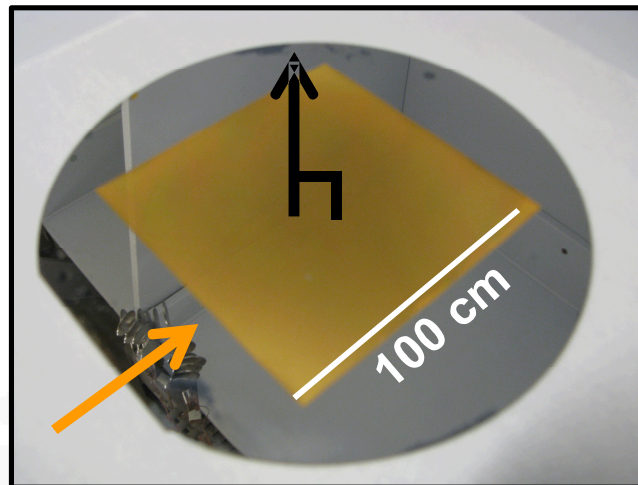
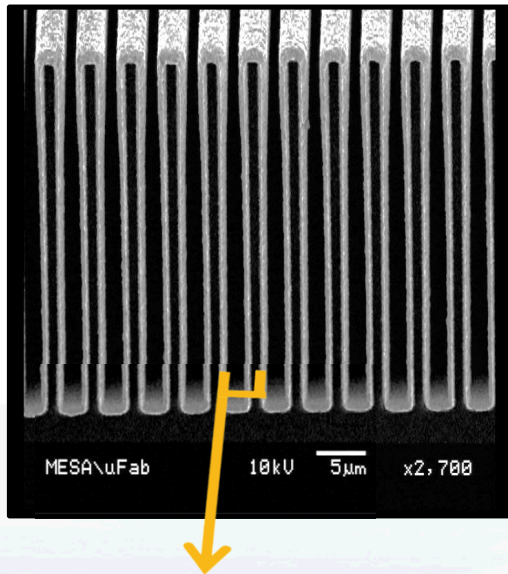




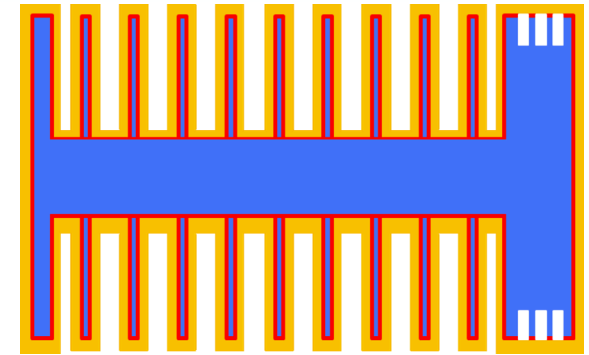
# Increase Effective Aspect Ratio of Gratings

Standard X-ray propagation direction

Alternative X-ray propagation direction

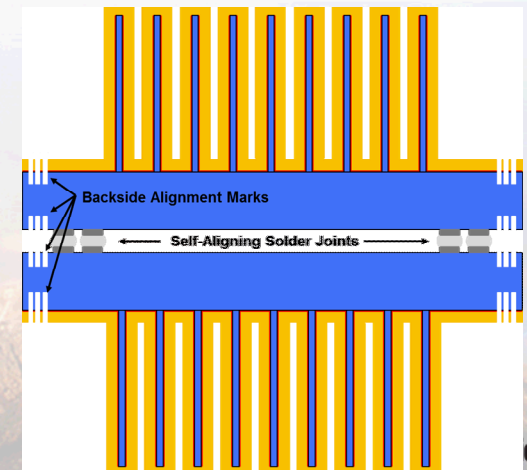


Front to Backside Alignment



ECD Au ALD Pt  
Silicon Solder Joint

Align and Stack  
Multiple Gratings



Orient x-ray k-vector down the length of the grating as opposed to perpendicular to the grating

- Effective aspect ratio increases to 10,000:1
- Decreases field of view from 100 cm x 100 cm down to 30 μm x 100 cm

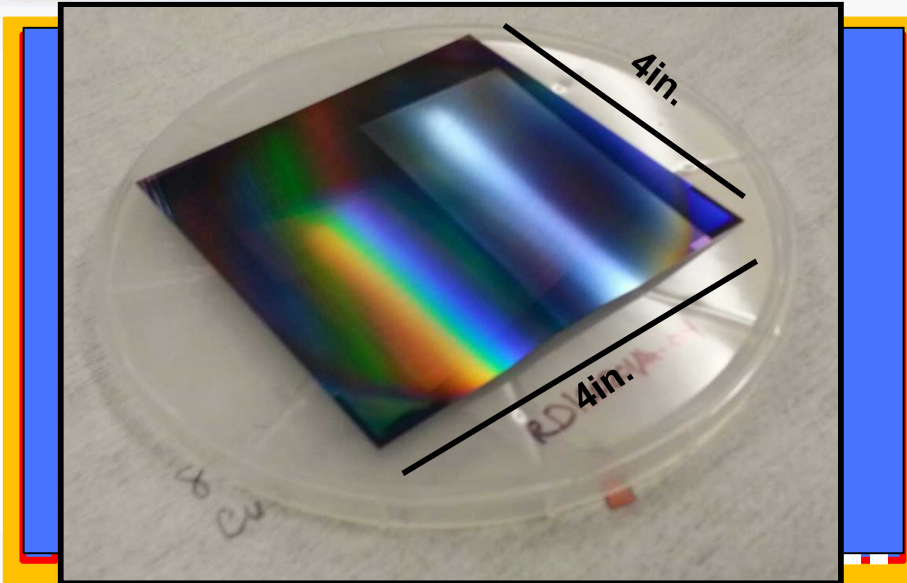




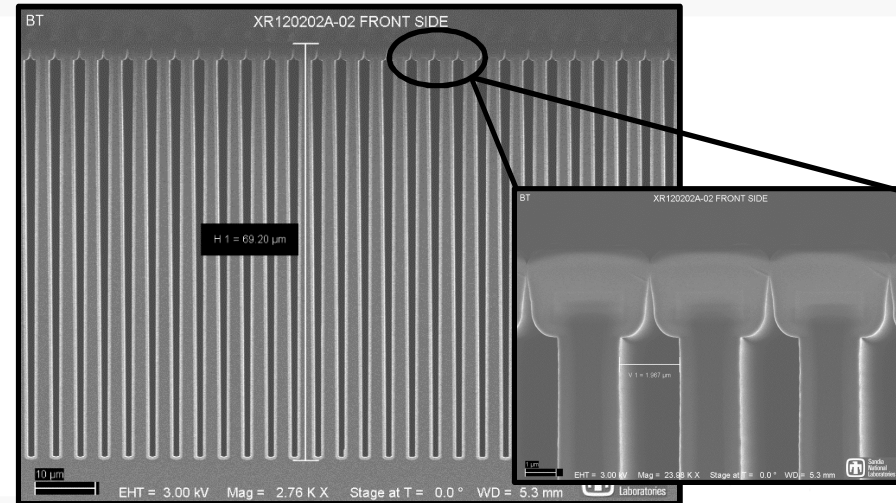
# Front to Backside Aligned Gratings

Large Fields of View Possible

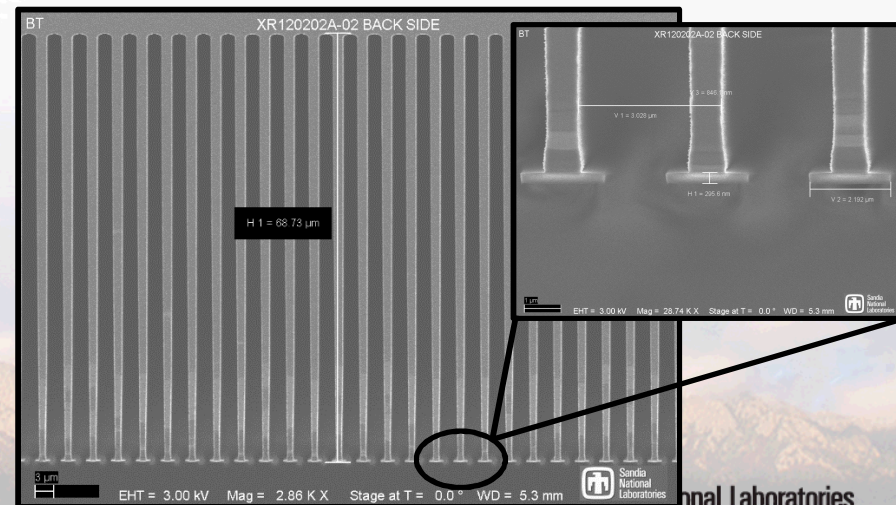
Silicon ALD PE ECD Au



## Oxide Coated Front Side Gratings

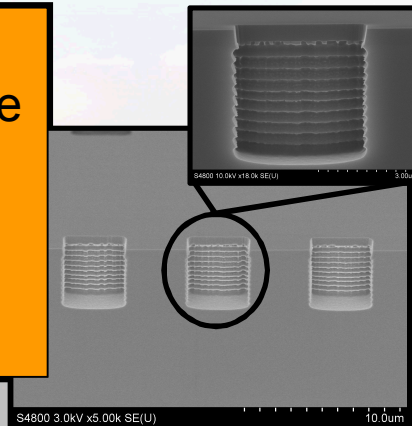


## Backside Gratings



## Backside Alignment (BSA) Marks

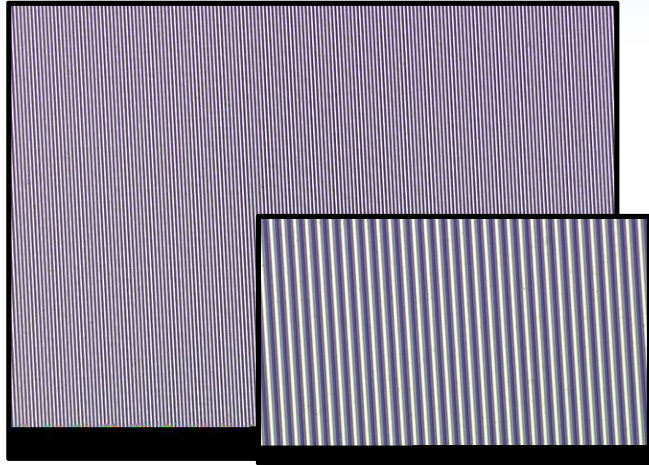
This image will be replaced by a similar one provided by and approved by Nikon



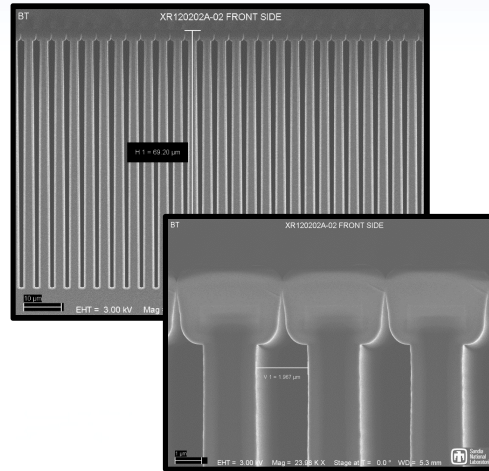


# Frontside Grating Oxide Removal

## Before Oxide Removal

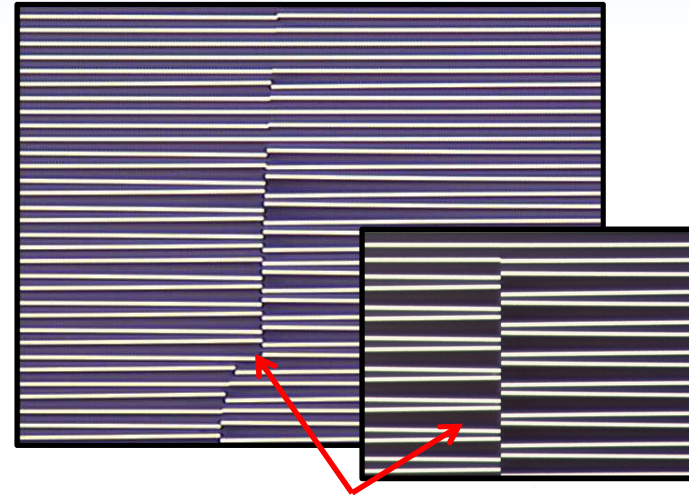


Top Down Optical Image



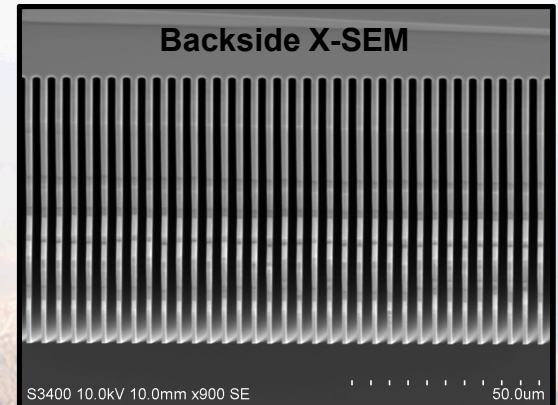
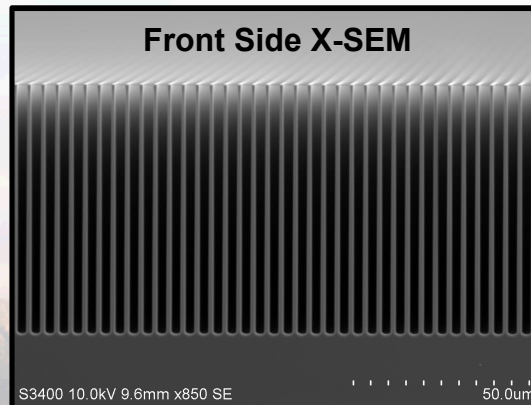
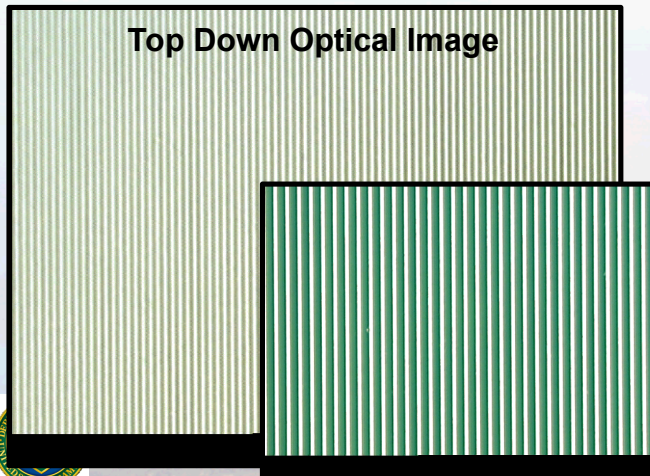
Cross-section SEM

## Buffer Oxide Etch (BOE) w/o Critical Point Dryer



Si grating breaks while chemistry is drying

## BOE with Critical Point Dryer



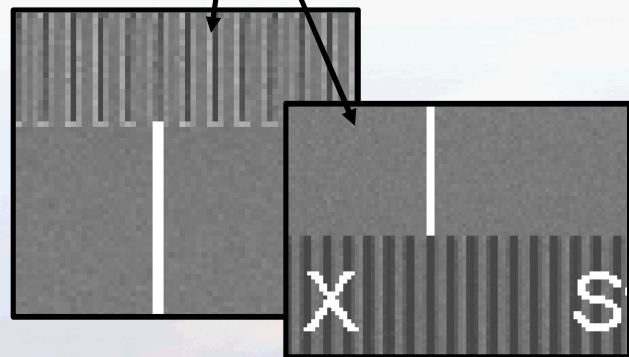
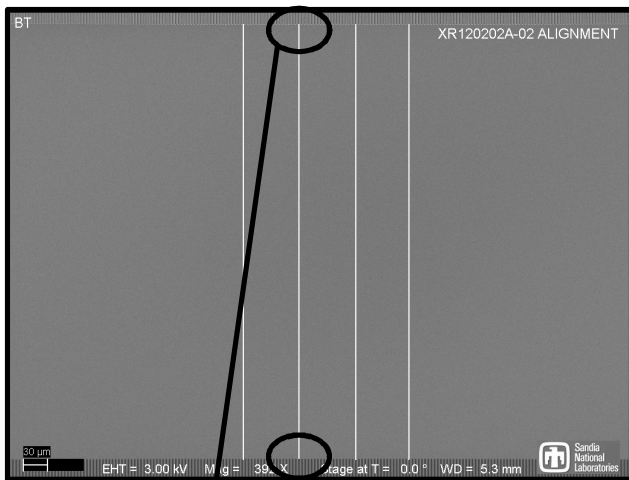
Critical point dryer reduces surface tension while chemistry dries protecting the Si grating



# Measuring Front to Back Alignment Accuracy

Large separation distance and small feature sizes make it difficult to obtain quantitative alignment measurements

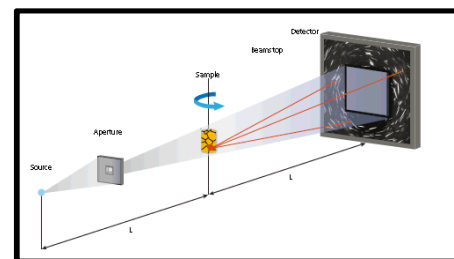
Cross-section SEM Image



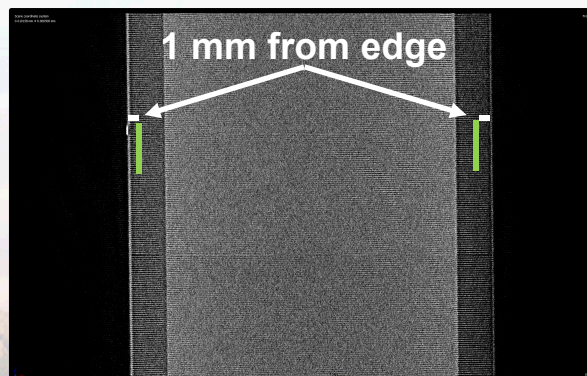
SEM imaging is not capable of quantifying alignment



Zeiss Xradia 520 Versa NanoCT System



Side view CT scan of BSA Gratings



Qualitatively our alignment is within  $0.5\text{ }\mu\text{m}$  as each pixel from the CT scan is  $0.5\text{ }\mu\text{m}$

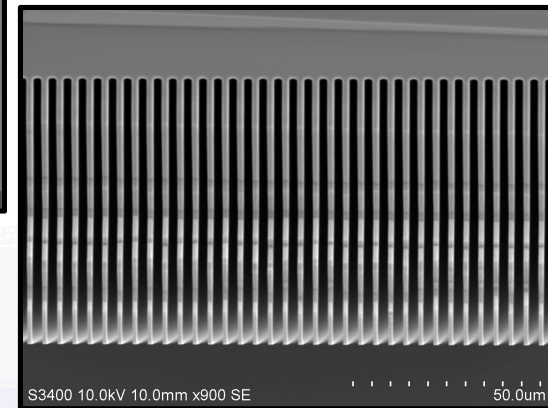
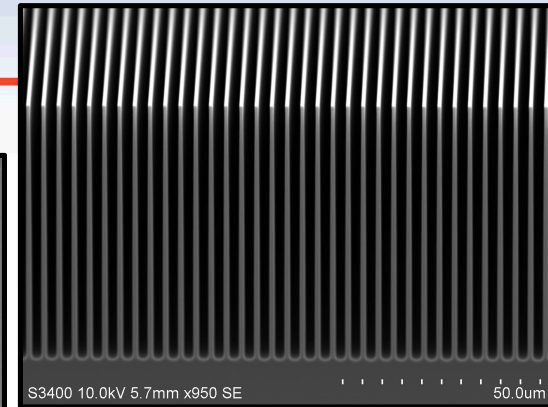
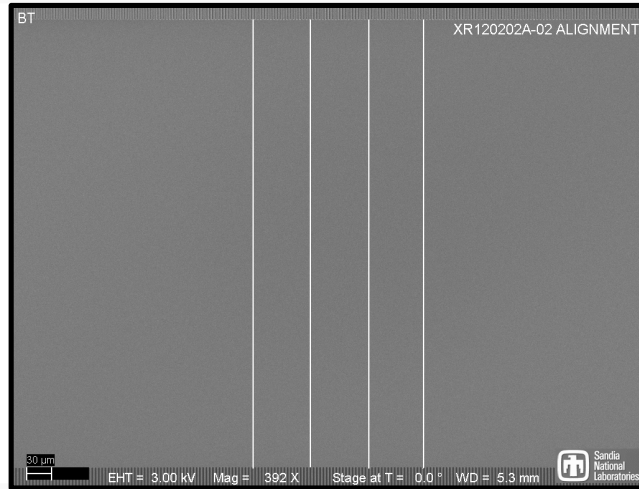
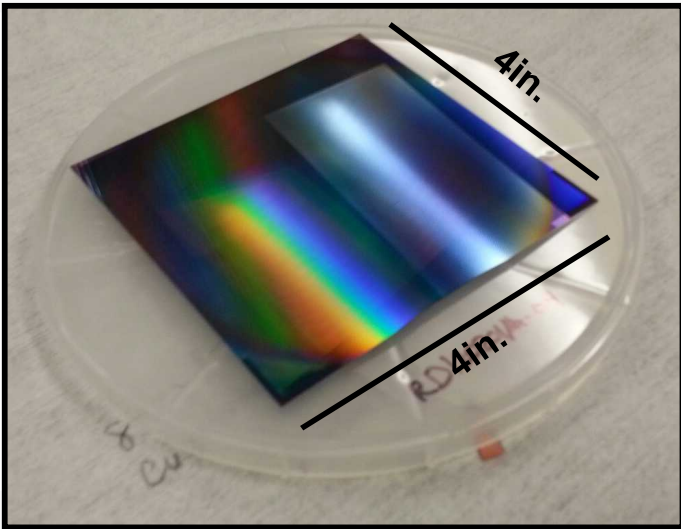
Superimposed Pitch Measurements



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# Summary



## Grating Fabrication with Front-to-Back Alignment

- Doubles the effective aspect ratio
- Cost effective material can be used to fill this template at current x-ray energies
- Higher x-ray energies possible with precision Au electroplating
- Large area fields of view possible

## Future Work

- Develop double sided Au electro-coating process
- Investigate precision alignment of multiple stacked gratings



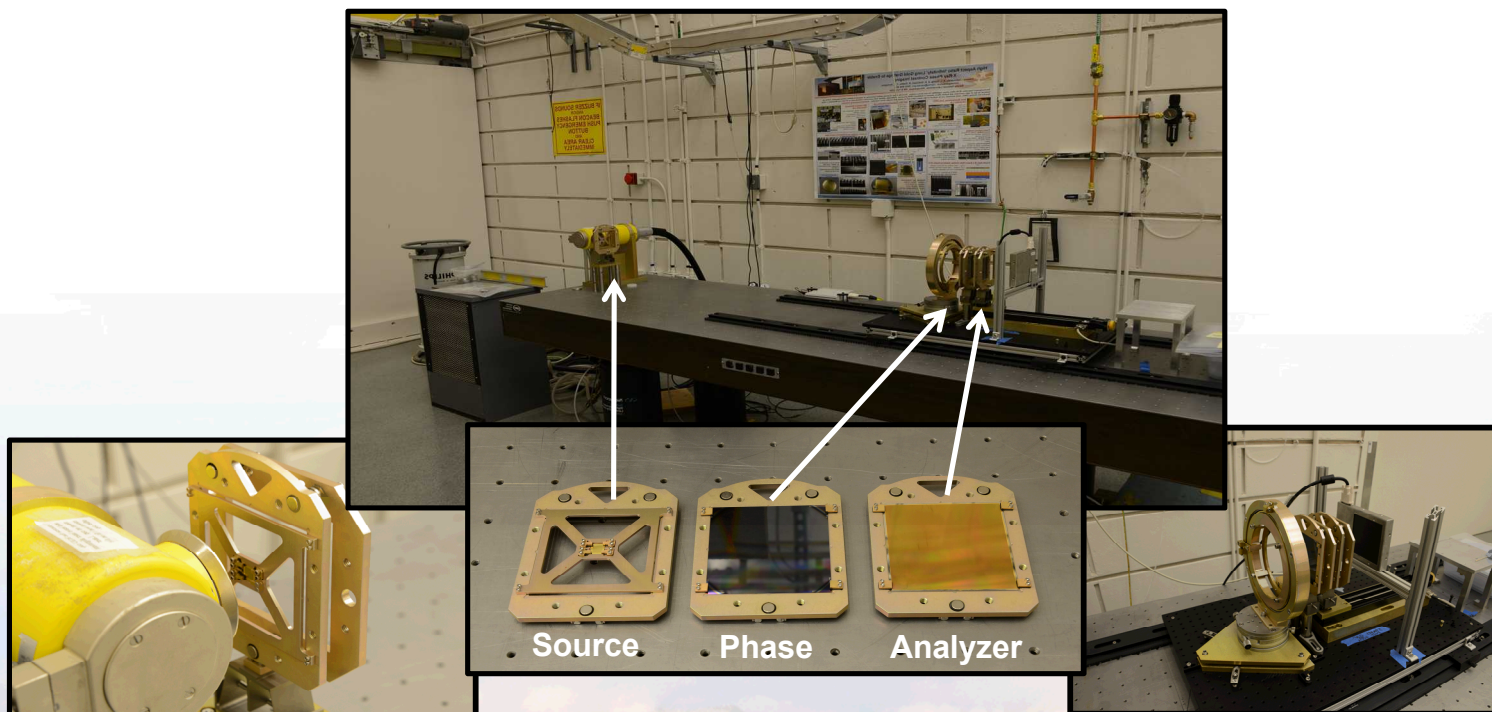


# Acknowledgements

Andrew Hollowell, Christian Arrington, Kalin Baca, Jonathan J. Coleman, Patrick Finnegan, Ryan Goodner, Steven Grover, Jeffrey Hunker, Jaime McClain, Kate Musick, Collin Smith, Kyle Thompson, Amber Dagel

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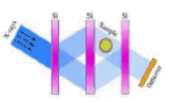
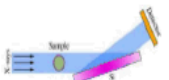
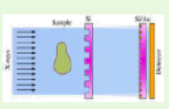
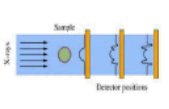
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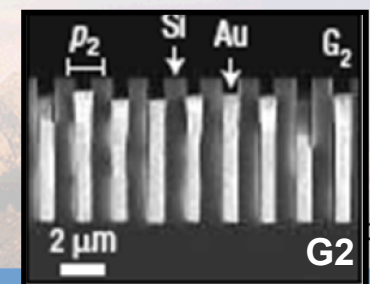
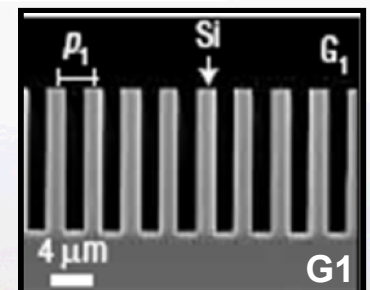
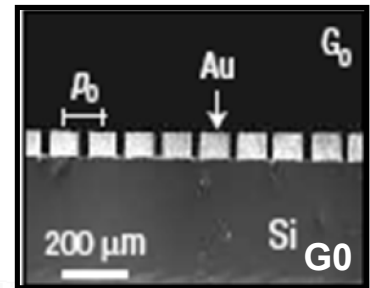
# 3 Grating System w/ Conventional X-Ray Tube

Method	working principles	setup scheme	measured phase quantity	PROS	CONS
Crystal interferometer	beam splitting and recombining crystals (Si)		phase $\phi$	<ul style="list-style-type: none"> <li>highest phase sensitivity</li> </ul>	<ul style="list-style-type: none"> <li>mechanical instability</li> <li>monochromatic (synchrotron)</li> <li>limited FOV (crystals)</li> <li>low efficiency</li> </ul>
Analyzer based interferometer	bragg reflection		phase gradient $\nabla \phi$	<ul style="list-style-type: none"> <li>high phase sensitivity</li> </ul>	<ul style="list-style-type: none"> <li>monochromatic (synchrotron)</li> <li>low efficiency</li> </ul>
Grating based interferometer	grating interference		phase gradient $\nabla \phi$	<ul style="list-style-type: none"> <li>good phase sensitivity</li> <li>polychromatic</li> <li>large FOV</li> <li>high efficiency</li> </ul>	<ul style="list-style-type: none"> <li>requires gratings</li> </ul>
Propagation based interferometer	Free space Fresnel propagation		Laplace of phase $\Delta \phi$	<ul style="list-style-type: none"> <li>simple design</li> <li>polychromatic</li> </ul>	<ul style="list-style-type: none"> <li>requires high-res detector</li> <li>low phase sensitivity</li> <li>low efficiency</li> </ul>

$$n = (1 - \delta) + i \cdot \beta$$

$\beta \rightarrow$  Absorption  $\delta \rightarrow$  Phase  
 $\delta / \beta = \sim 10^3$

Phase imaging is  $\sim 10^3$  times higher Sensitivity than absorption imaging



## G0 – Source Absorption Grating

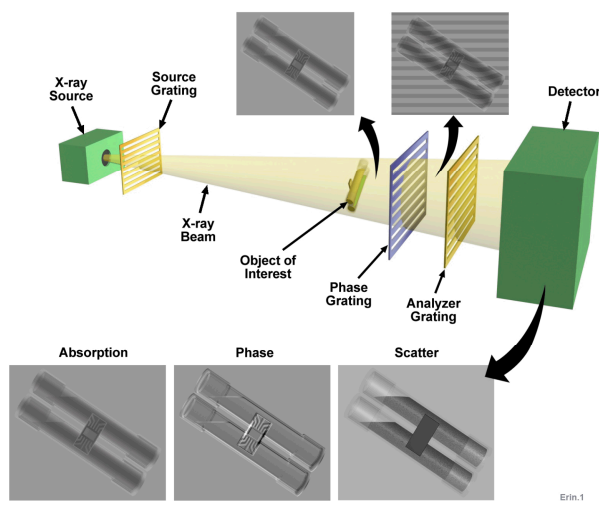
Creates an array of individually coherent but mutually incoherent sources

## G1 – Phase Grating

Creates zero and  $\pi$  phase shifts to form an interference pattern at G2 plane

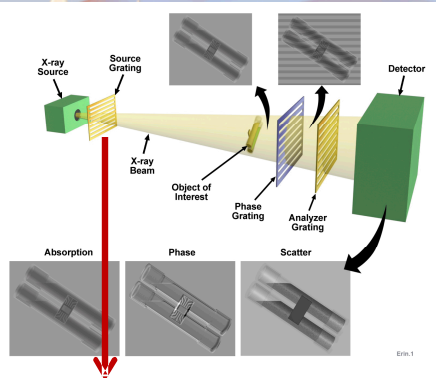
## G2 – Analyzer Absorption Grating

Modulate the interference signal on detector (local fringe position  $\rightarrow$  single intensity variation recorded by detector)

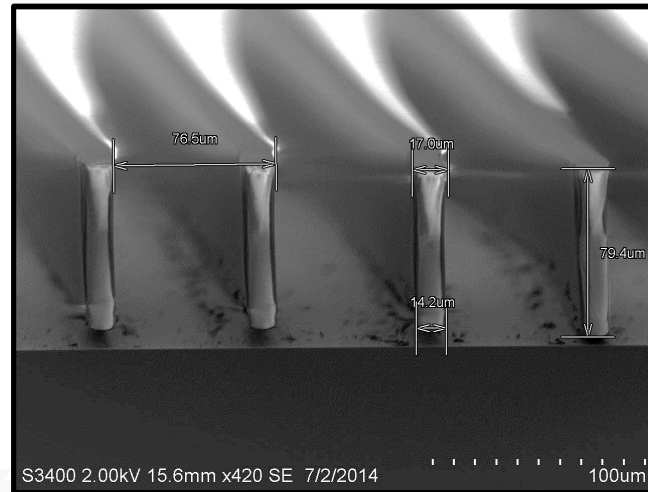




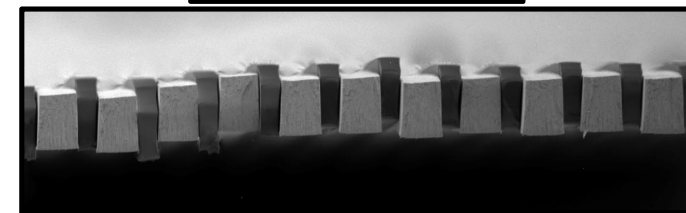
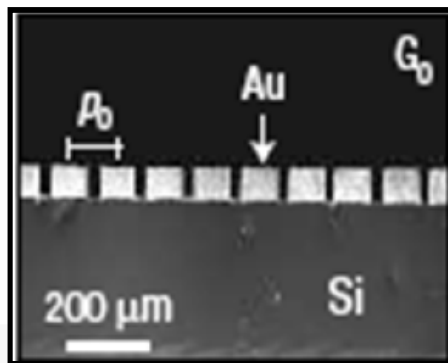
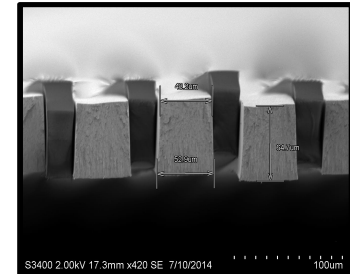
# G0 Source Grating – UV Photoresist



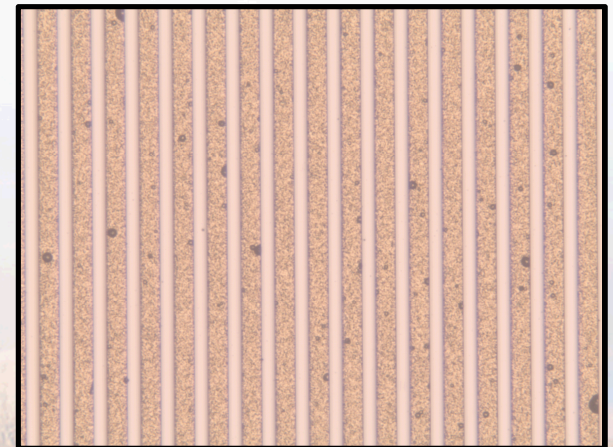
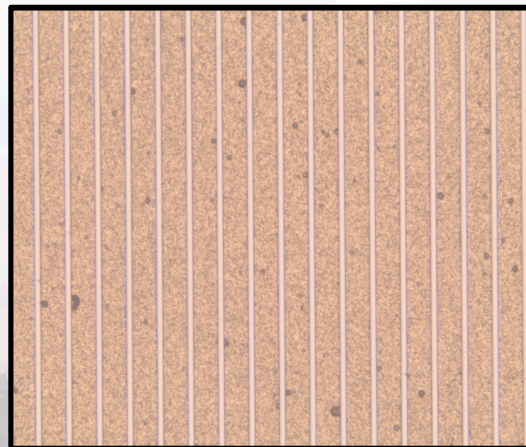
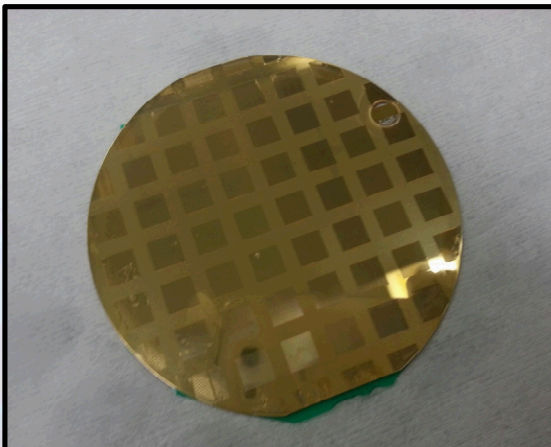
## KMPR Negative Photoresist



## 65μm Thick Au



## Delamination result of cross-section



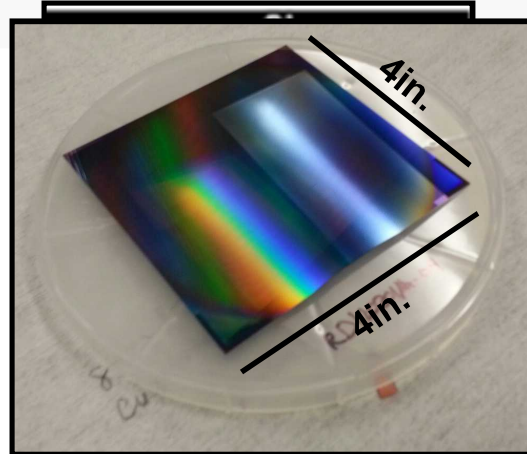
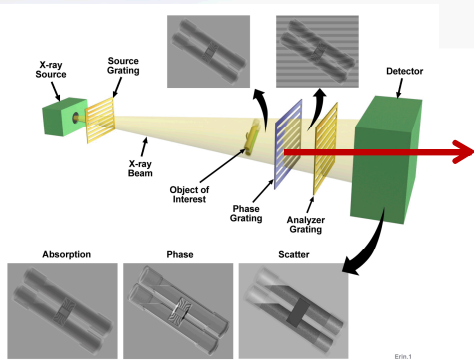
Pitch: 76, 77, 78, 79, 80μm - Linewidth: 13, 18, 23, 28μm  
Thickness: 65μm, Highest Aspect Ratio of 5:1



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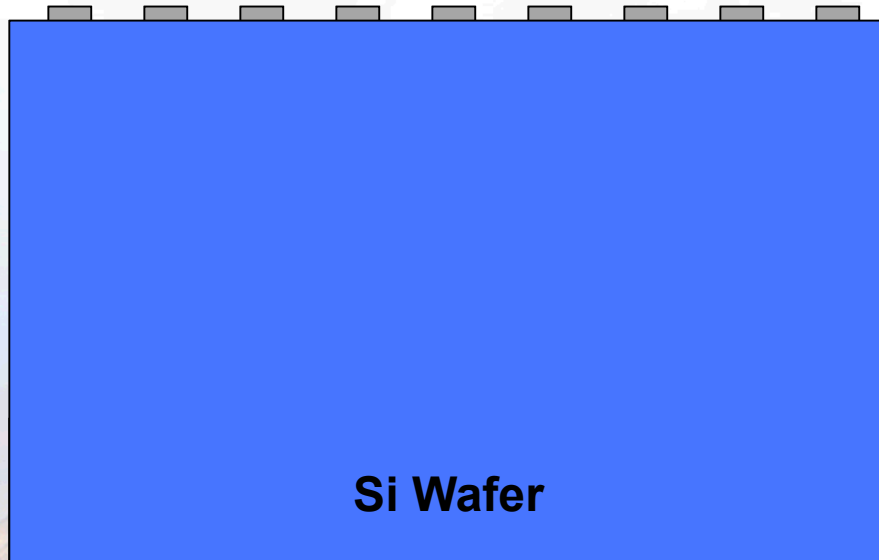
# G1 Phase Grating – Si Etching



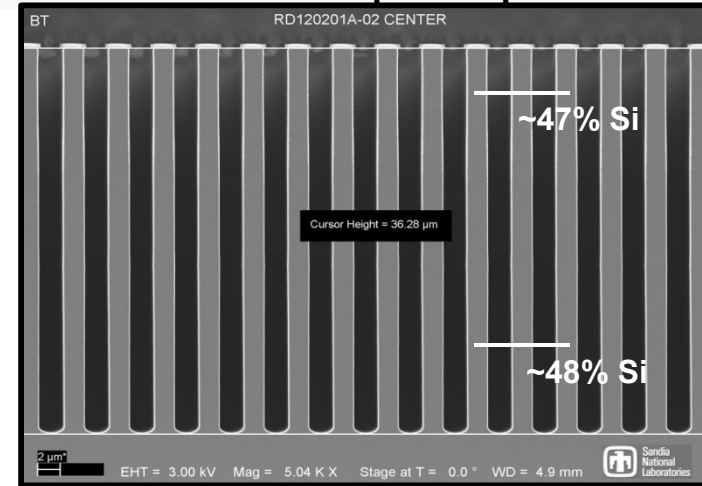
4 $\mu$ m Period Si



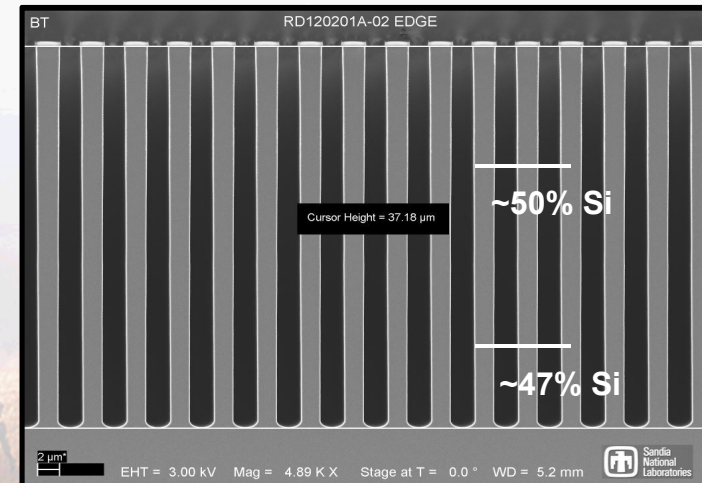
2 $\mu$ m wide Si



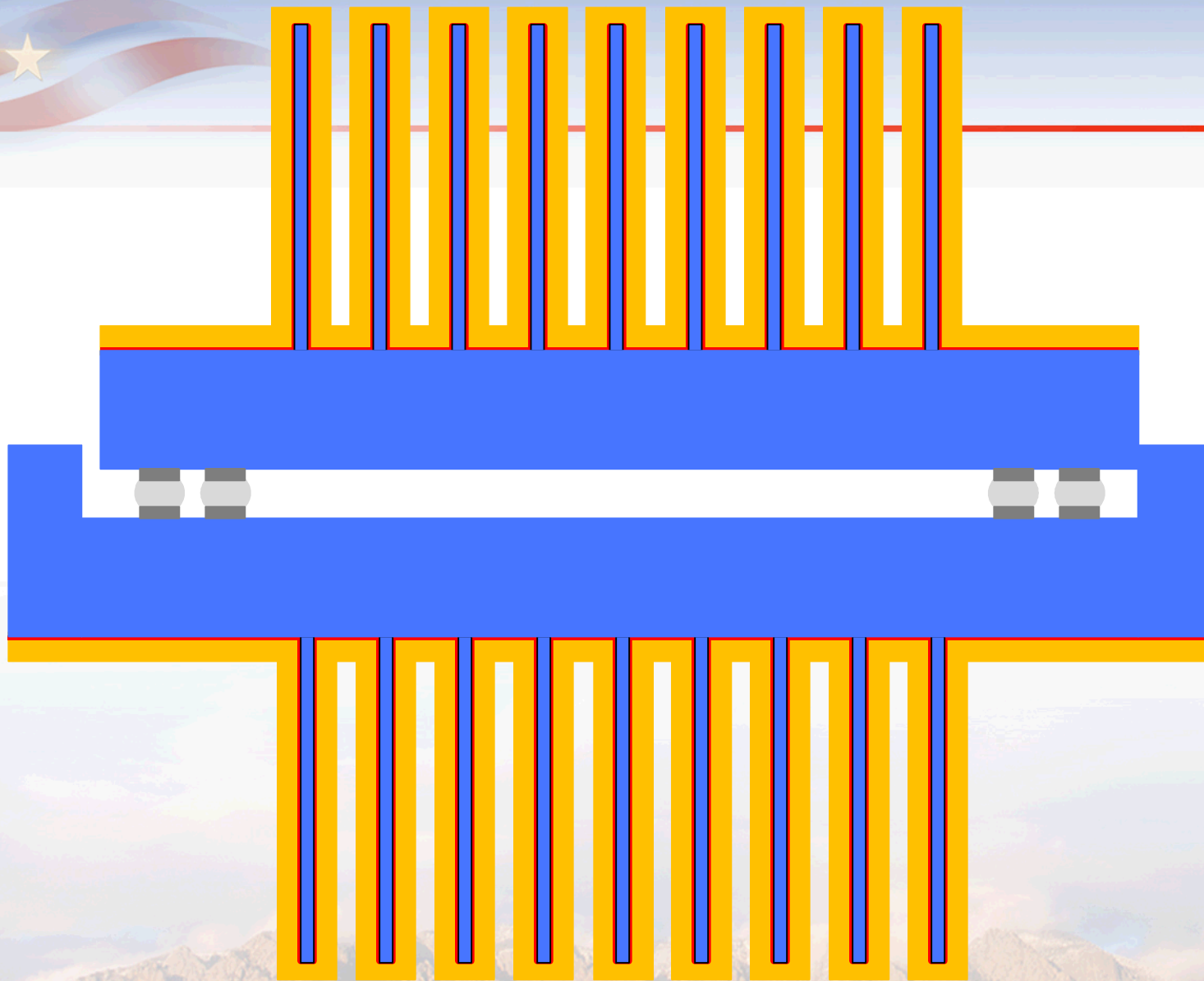
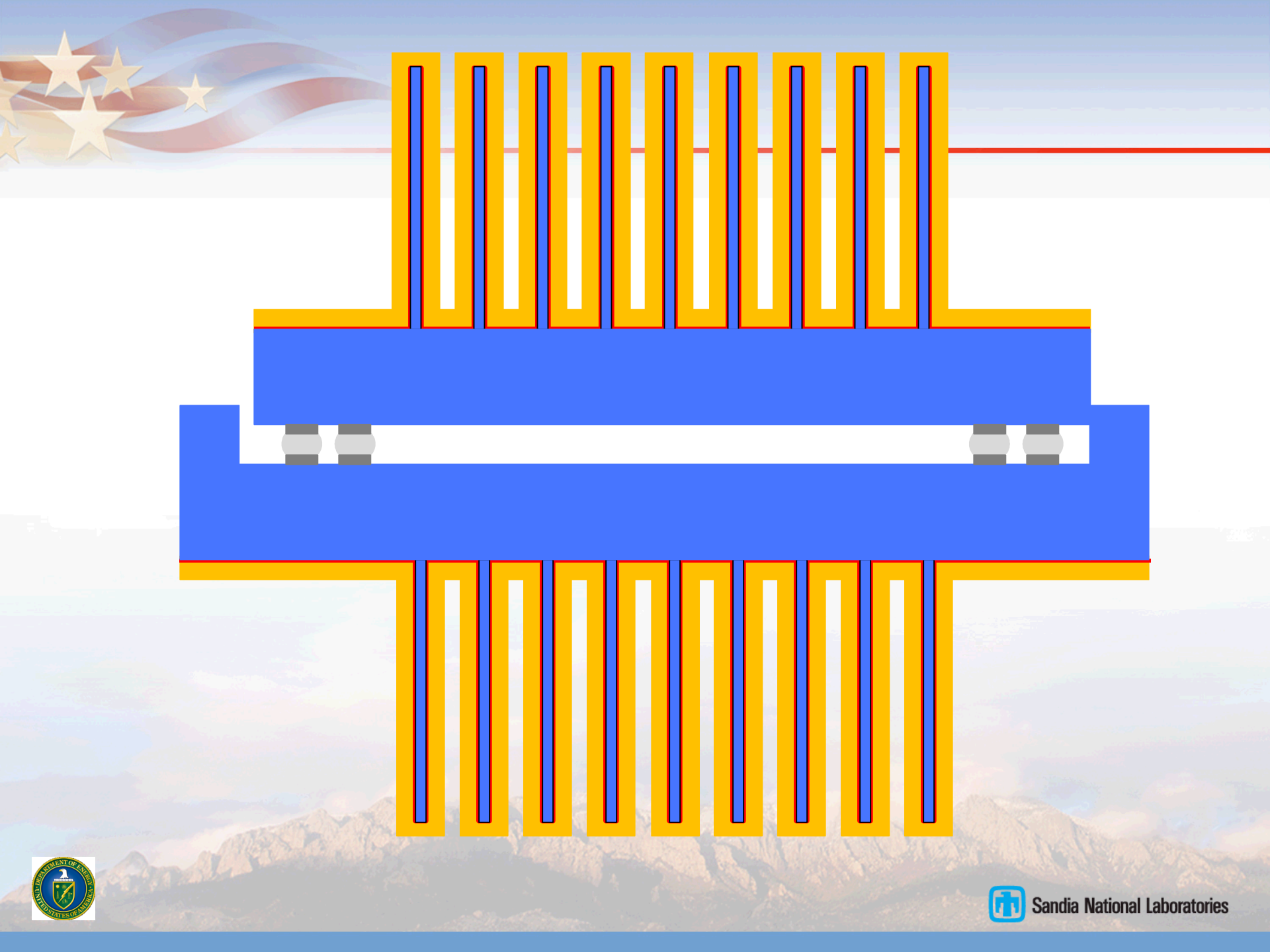
Center 36 $\mu$ m deep



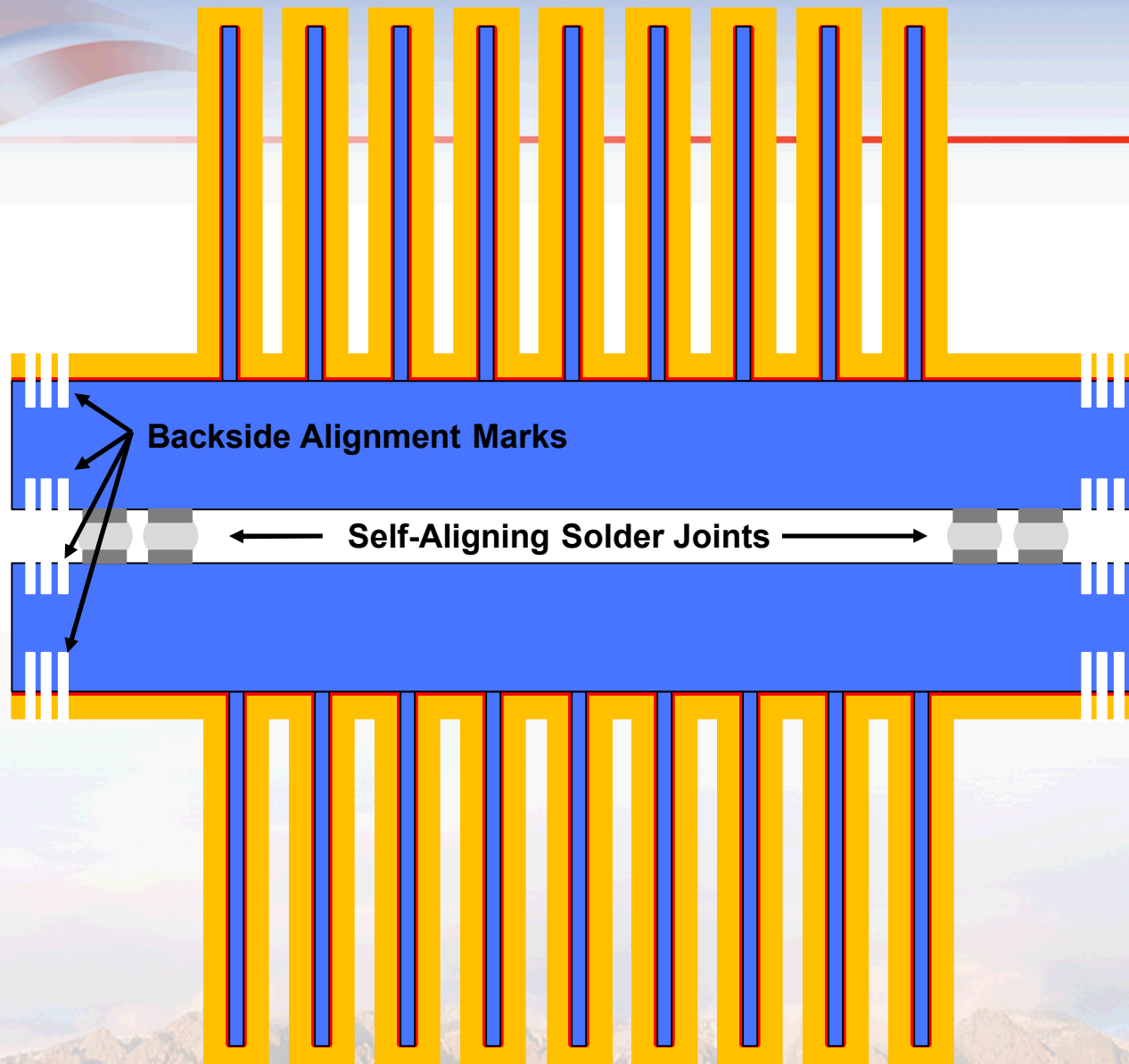
Edge 37 $\mu$ m deep





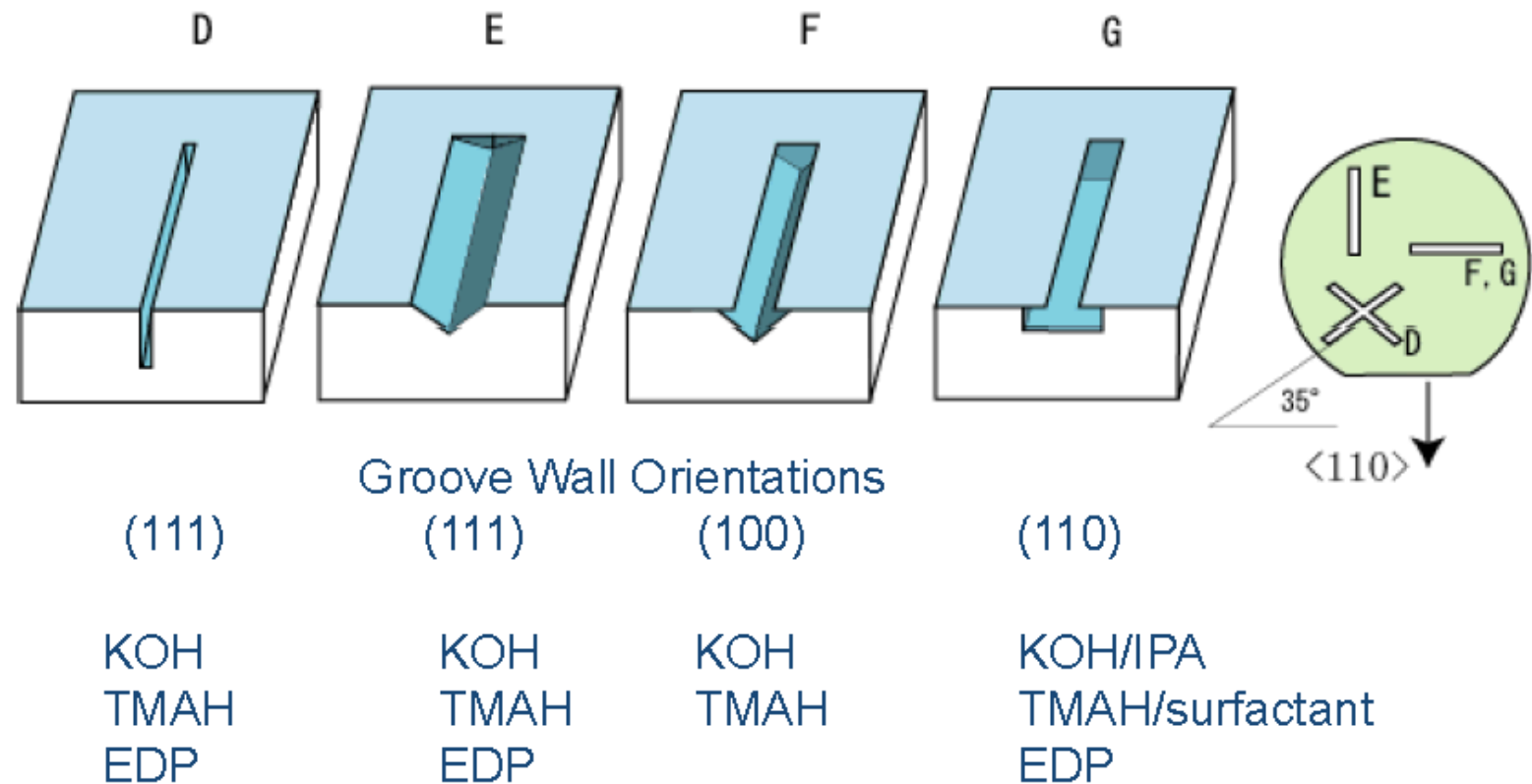








# Variation in etching profile on (110) silicon wafer



Basic 2 Anisotropic Wet-etching of Silicon:  
Characterization and Modeling of Changeable Anisotropy  
COE for Education and Research of Micro-Nano Mechatronics, Nagoya University

Prof. K. Sato

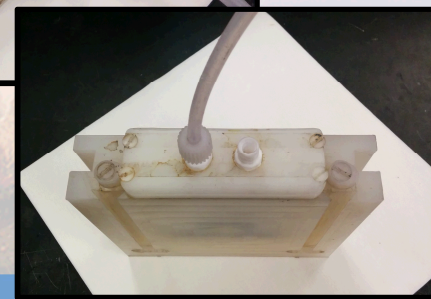
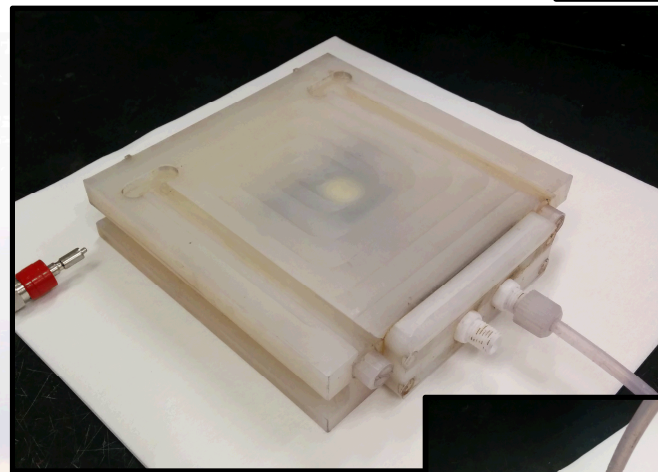
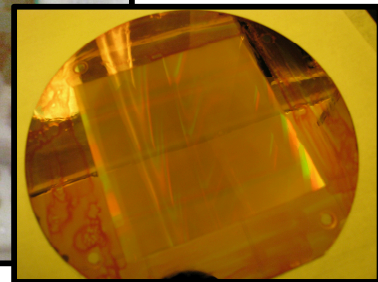
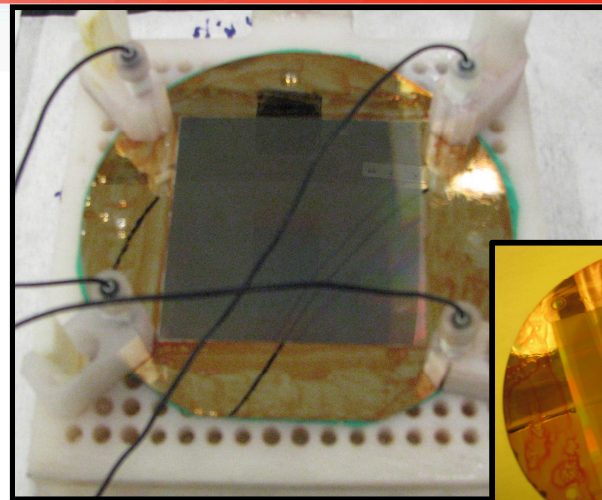
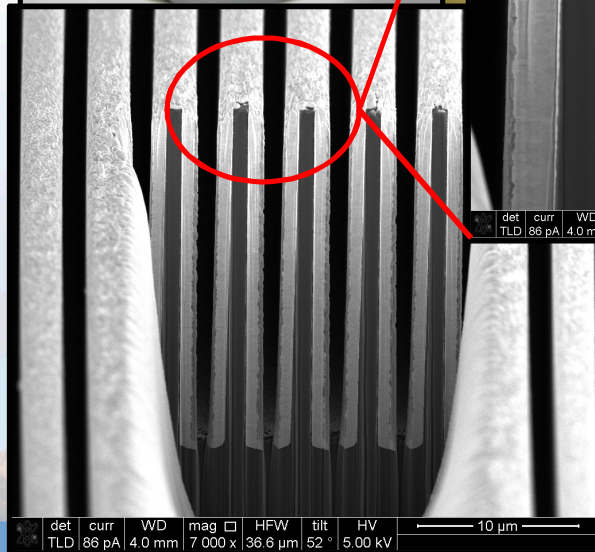
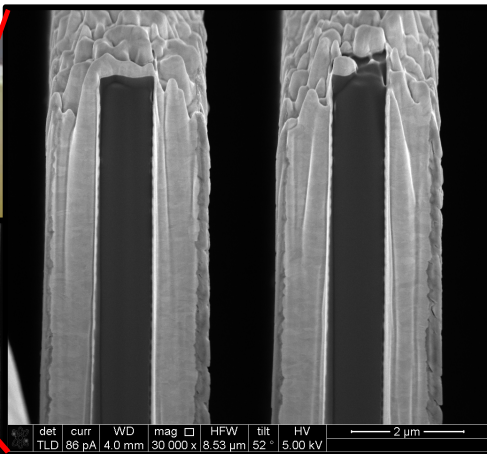
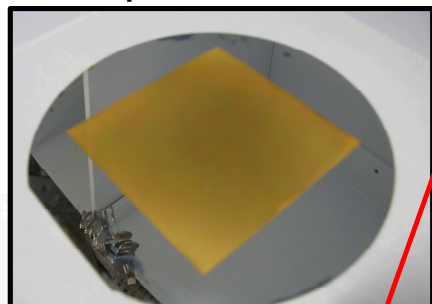


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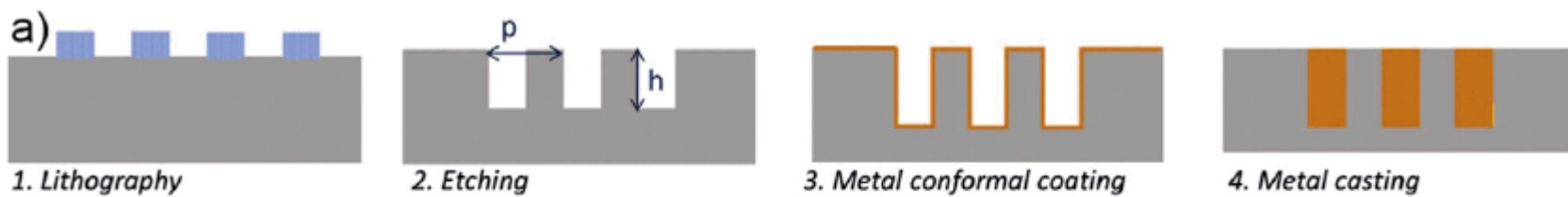


# Chemistry Flow and Fixture Modifications to Realize 16in.<sup>2</sup> Uniformity

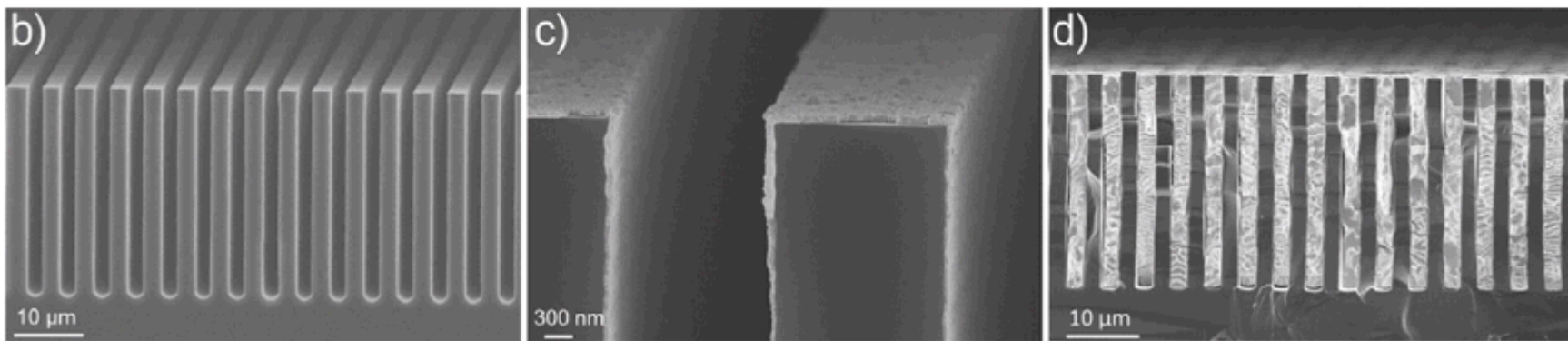
- Chemistry flow dictates ionic replenishment
- Multiple contact points evenly distributes conductivity
- Vibrating fixture enables even solution replenishment and ionic distribution







A1



L. Romano et. al. Microelectronic Engineering 176(2017) 6-10





## Slide 26

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**A1**

Andrew , 8/30/2017



# Vapor Hydrofluoric Acid (VHF)

